

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 7,352,606 B2
APPLICATION NO. : 10/694165
DATED : April 1, 2008
INVENTOR(S) : Luc Wuidart

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It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

On the Title Page, in the Abstract:

line 1 should read:

A monotonic counter formed as an integrated circuit, each

line 3 should read:

at least one memorization element formed of a polysilicon

In Column 1,

line 8 should read:

more specifically, to monotonic counters with an irrevers-

line 11 should read:

Currently, to form monotonic up-counters, fuse ele-

line 42 should read:

which would be likely to be used in monotonic counting

line 48 should read:

The present invention aims at providing a monotonic

line 57 should read:

form a monotonic counter, the counting of which is com-

line 60 should read:

of a monotonic counter by using conventional MOS-type

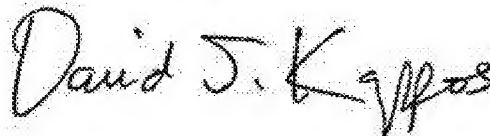
line 63 should read:

provides a monotonic counter formed as an integrated

line 65 should read:

containing at least one storage element formed of a

Signed and Sealed this
Eighth Day of May, 2012

A handwritten signature in black ink that reads "David J. Kappos". The signature is written in a cursive, flowing style with a large initial "D" and a stylized "K".

David J. Kappos
Director of the United States Patent and Trademark Office

CERTIFICATE OF CORRECTION (continued)

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In Column 2,

line 57 should read:

The same elements have been designated with the same reference

line 65 should read:

an irreversible monotonic counter is desired.

line 66 should read:

A feature of the present invention is to form a monotonic

In Column 3,

line 2 should read:

the storage element of each counting cell is formed of

In Column 9,

line 45 should read:

forming a perfectly reliable monotonic counter, the pro-

line 55 should read:

monotonic counter. It should however be noted that,

In Column 10,

line 22 should read:

resistive storage polysilicon element, programmable

In the Claims

Col. 12, claim 17, line 19 should read:

decreased, thereby programming the monotonic